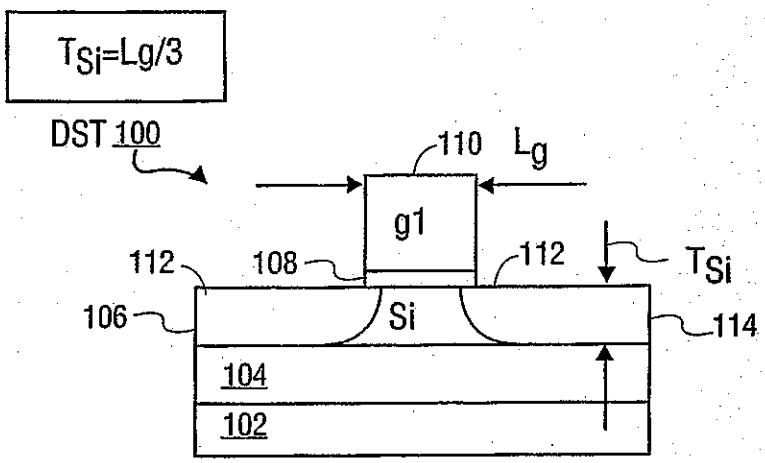

$T_{Si}$=Lg/3
DST 100
110
Lg
g1
112
108
112
$T_{Si}$
106
Si
114
104
102

FIG. 1

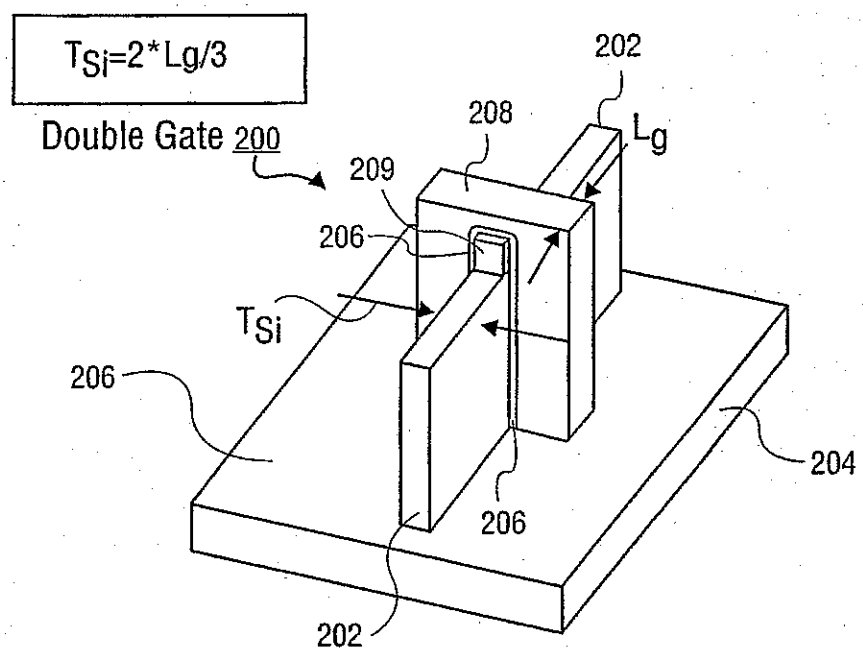

$T_{Si}$=2*Lg/3
Double Gate 200
202
208
Lg
209
206
$T_{Si}$
206
204
206
202

FIG. 2A

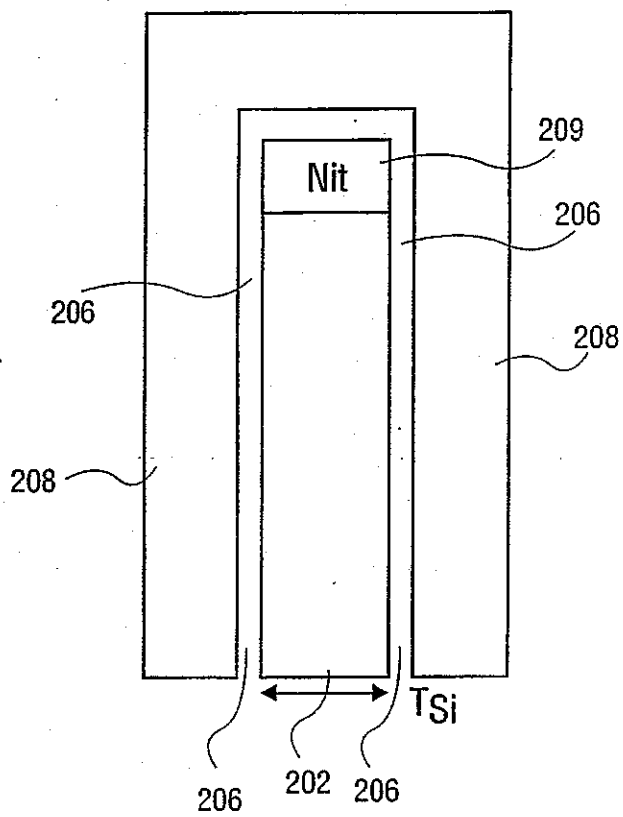



FIG. 2B

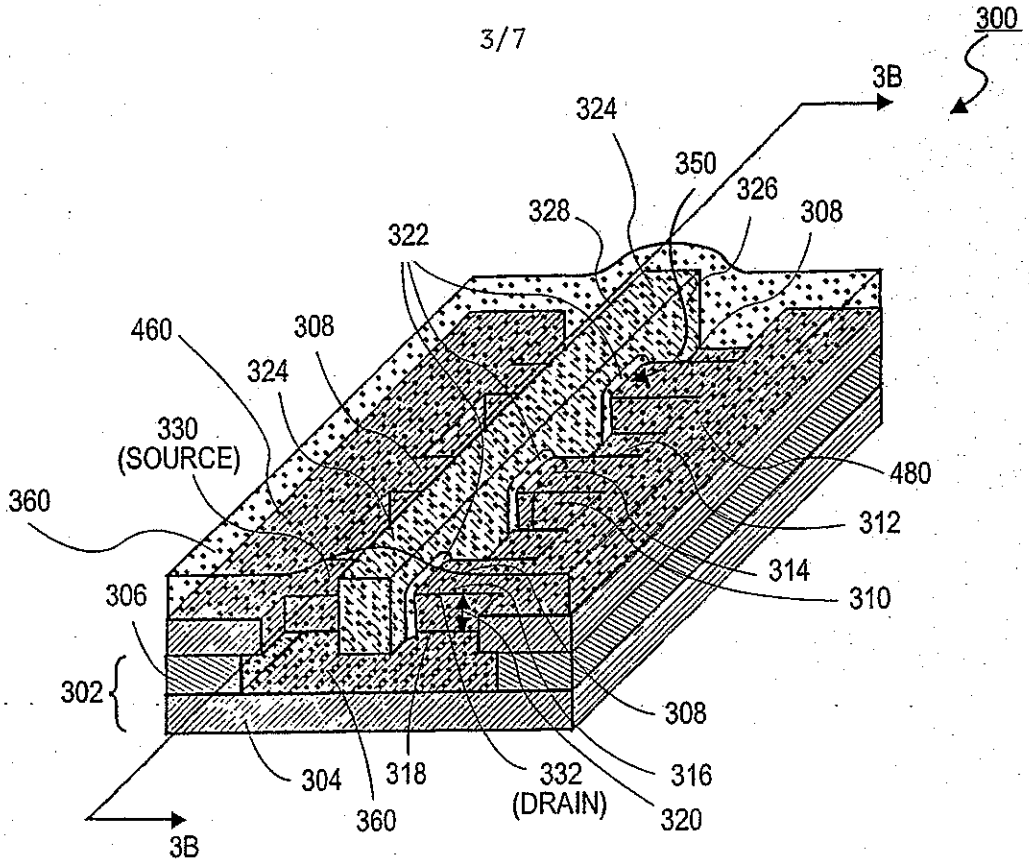

300
3B
324
350
326
328
308
322
460
308
324
330
(SOURCE)
480
360
312
314
310
306
302
308
304
318
332
(DRAIN)
316
320
360
3B

FIG. 3A

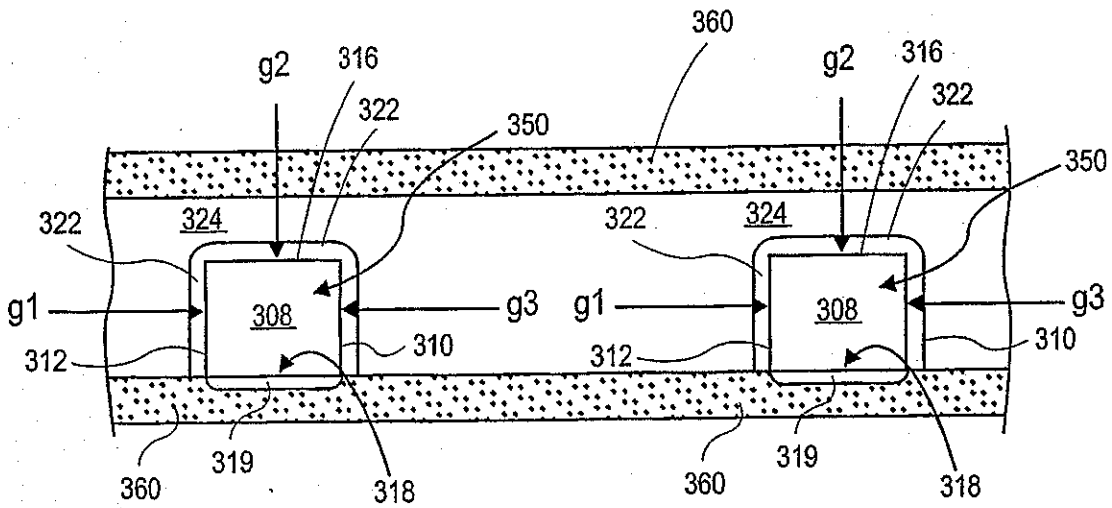

360
g2
316
322
350
g2
316
322
350
322
324
322
324
g1
308
g3
g1
308
g3
312
310
312
310
360
319
318
360
319
318

FIG. 3B

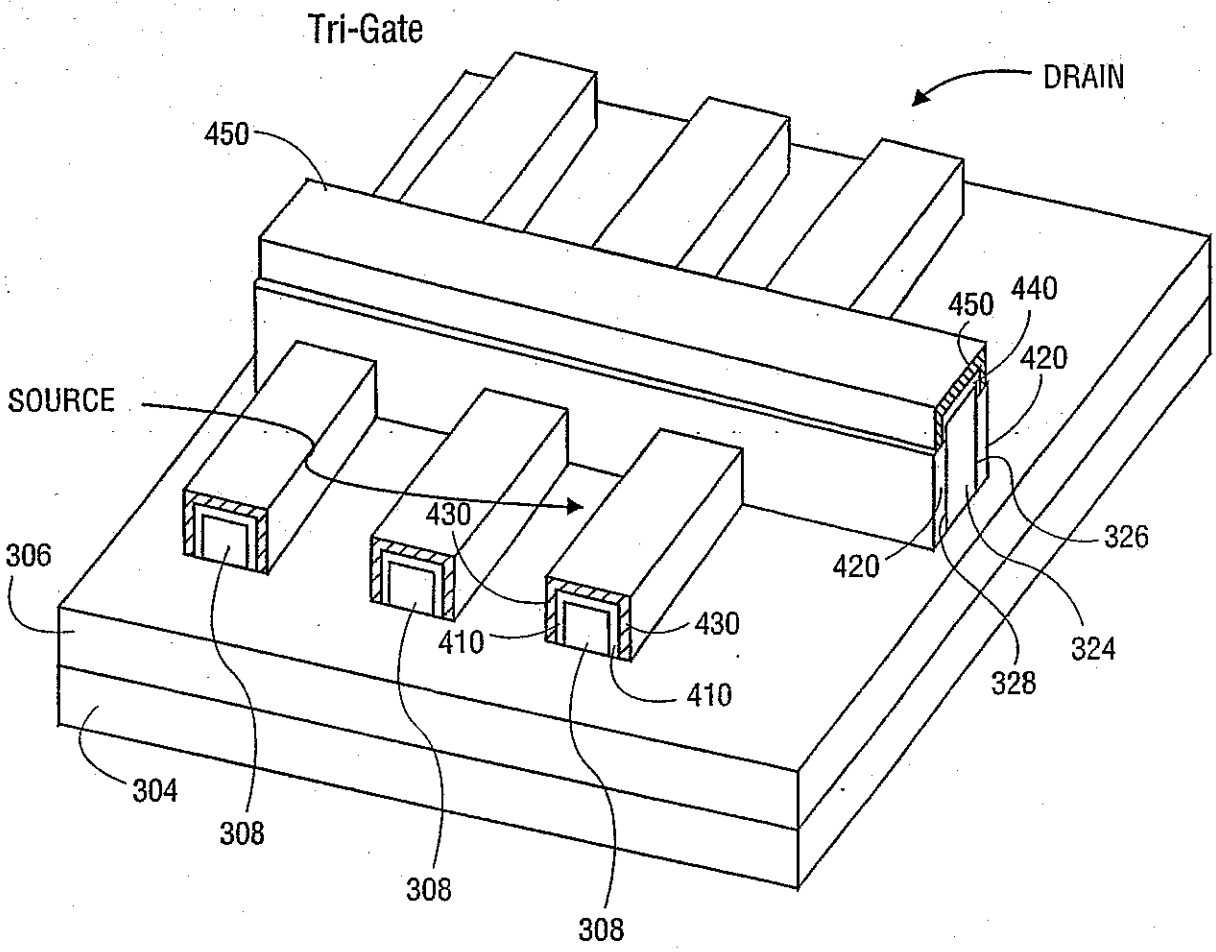

Tri-Gate
DRAIN
450
450
440
420
SOURCE
326
306
430
420
410
430
324
328
410
304
308
308
308

FIG. 4

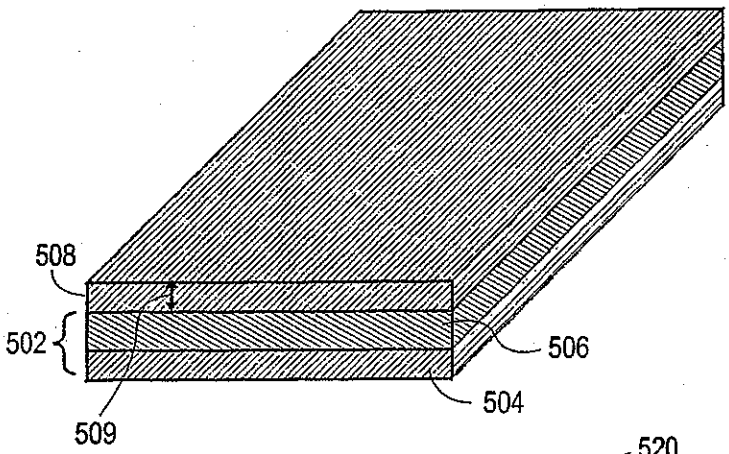



FIG. 5A

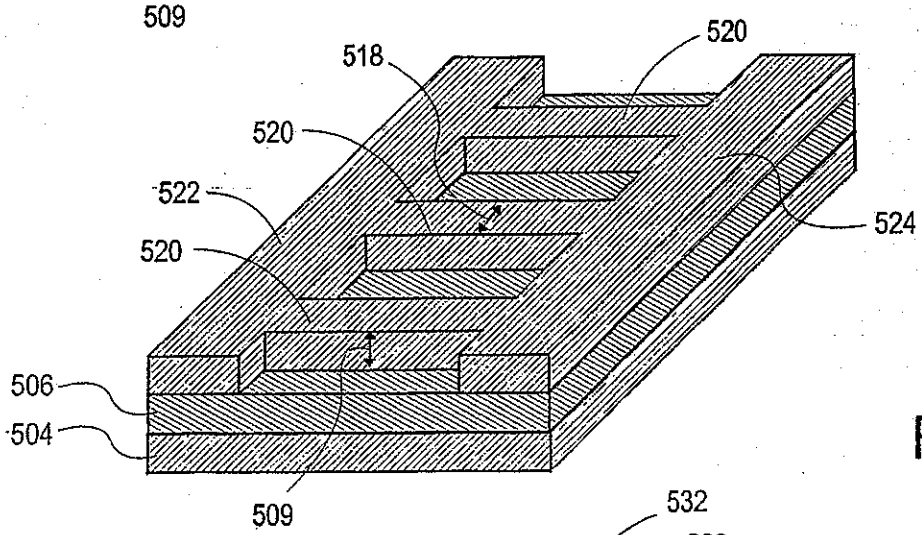



FIG. 5B

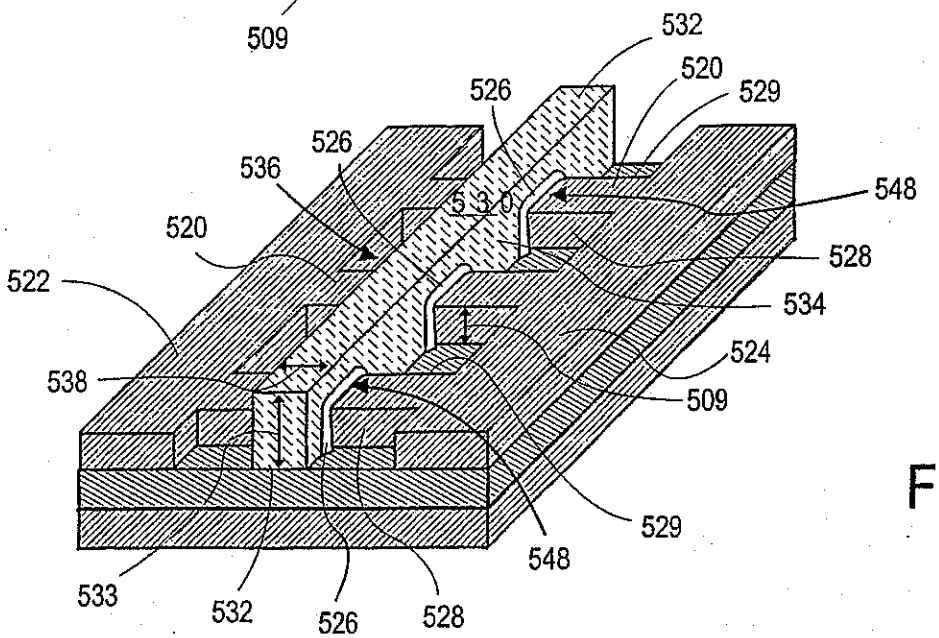



FIG. 5C

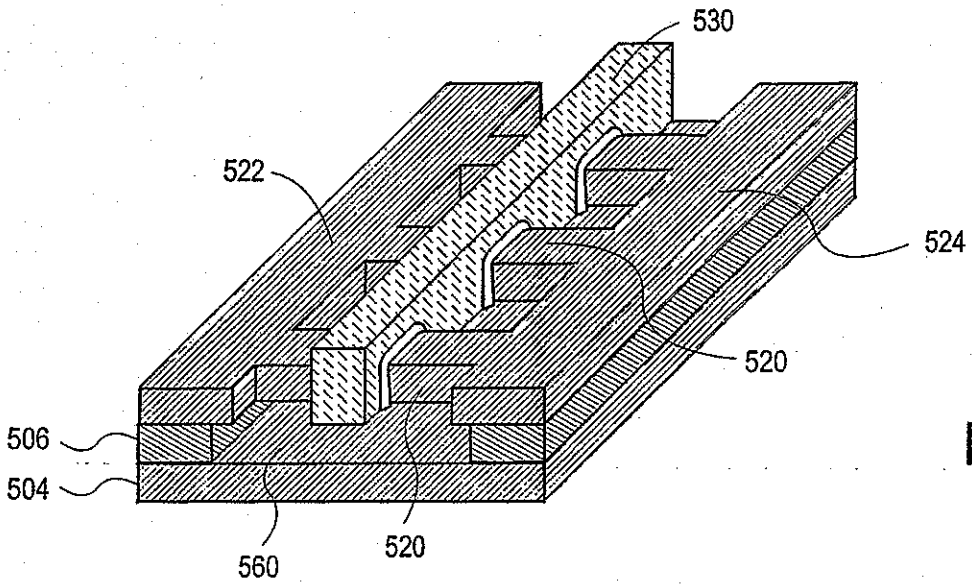

530
522
524
520
506
504
560
520

FIG. 5D

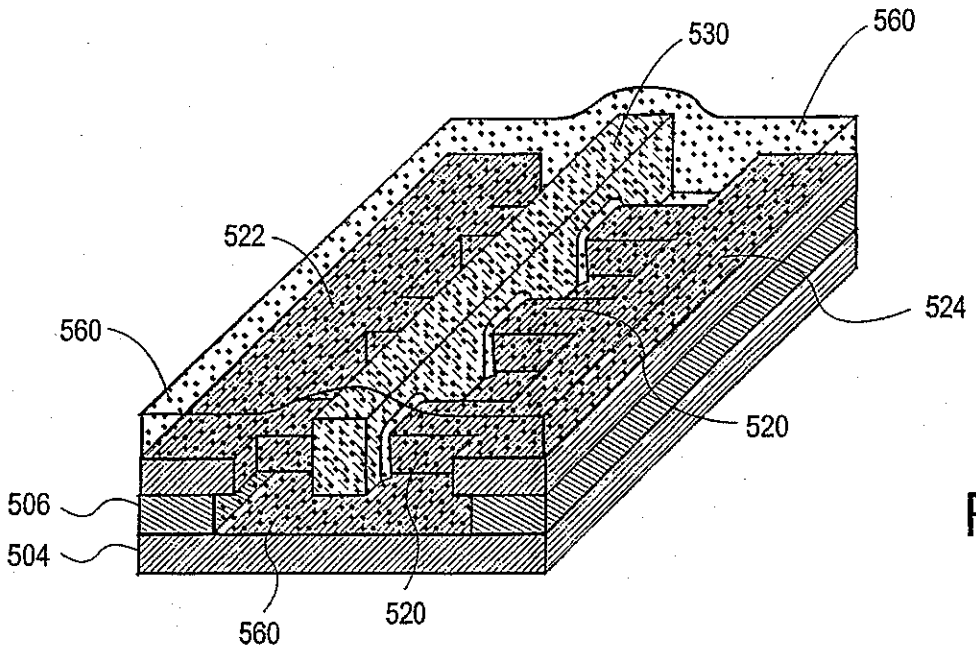

530
560
522
524
560
520
506
504
560
520

FIG. 5E

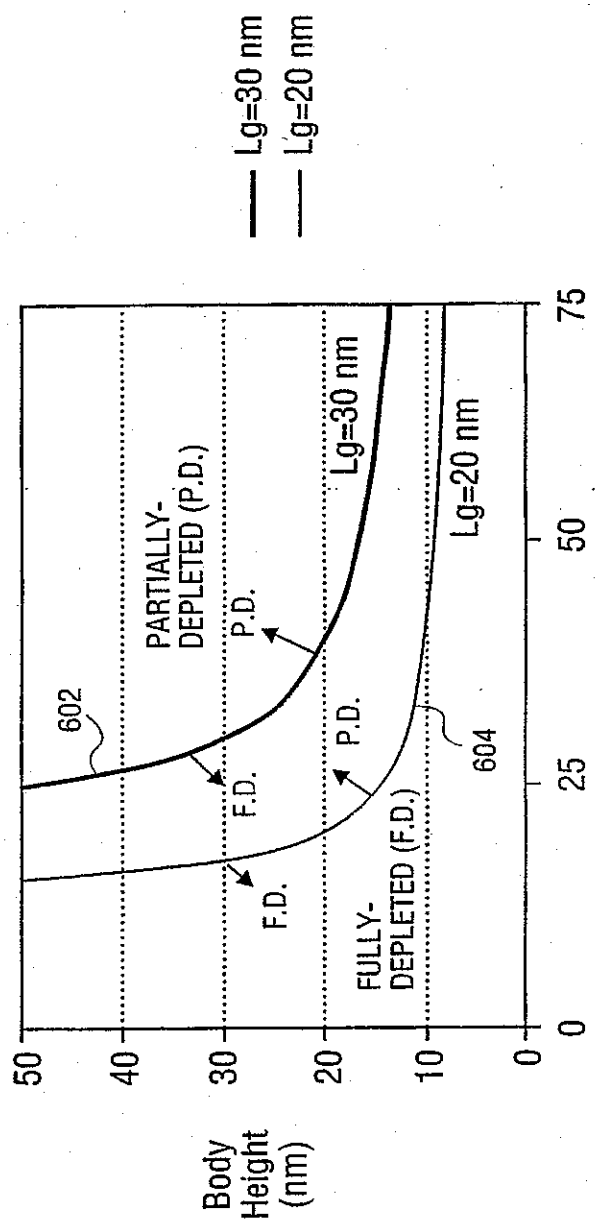

Lg=30 nm
Lg=20 nm
PARTIALLY-DEPLETED (P.D.)
FULLY-DEPLETED (F.D.)
P.D.
F.D.
P.D.
F.D.
Lg=30 nm
Lg=20 nm
602
604
Body Height (nm)
Body Width (nm)
50
40
30
20
10
0
0
25
50
75

FIG. 6